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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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2SK3235

Silicon N Channel MOS FET
High Speed Power Switching

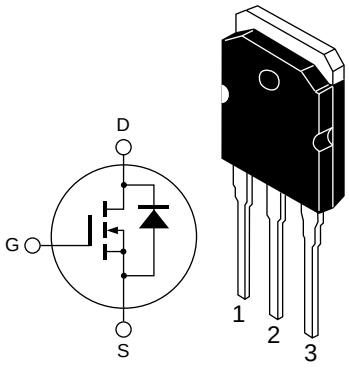
ADE-208-1371 (Z)
1st. Edition
Mar. 2001

Features

- Low on-resistance: $R_{DS(on)}$ = 0.3 Ω typ.
- Low leakage current: IDSS = 1 μA max (at VDS = 500 V)
- High speed switching: tf = 50 ns typ (at VGS = 10 V, VDD = 250 V, ID = 7.5 A)
- Low gate charge: Qg = 48 nC typ (at VDD = 400 V, VGS = 10 V, ID = 15 A)
- Avalanche ratings

Outline

TO-3P



1. Gate
2. Drain (Flange)
3. Source

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V_{DSS}	500	V
Gate to source voltage	V_{GSS}	±30	V
Drain current	I_D	15	A
Drain peak current	$I_{D\ (pulse)}$ Note1	60	A
Body-drain diode reverse drain current	I_{DR}	15	A
Body-drain diode reverse drain peak current	$I_{DR\ (pulse)}$ Note1	60	A
Avalanche current	I_{AP} Note3	15	A
Channel dissipation	Pch Note2	150	W
Channel to case Thermal Impedance	θ ch-c	0.833	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%
2. Value at Tc = 25°C
3. Tch ≤ 150°C

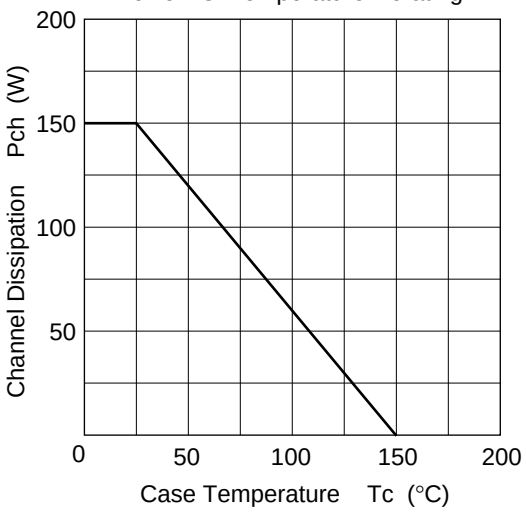
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	500	—	—	V	I_D = 10 mA, V_{GS} = 0
Gate to source leak current	I_{GSS}	—	—	±0.1	μA	V_{GS} = ±30 V, V_{DS} = 0
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	V_{DS} = 500 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	—	4.0	V	V_{DS} = 10 V, I_D = 1 mA
Static drain to source on state resistance	$R_{DS(on)}$	—	0.3	0.4	Ω	I_D = 7.5 A, V_{GS} = 10 V [Note4]
Forward transfer admittance	$\|y_{fs}\|$	8.5	14	—	S	I_D = 7.5 A, V_{DS} = 10 V [Note4]
Input capacitance	Ciss	—	1920	—	pF	V_{DS} = 25 V
Output capacitance	Coss	—	220	—	pF	V_{GS} = 0
Reverse transfer capacitance	Crss	—	30	—	pF	f = 1 MHz
Turn-on delay time	td(on)	—	35	—	ns	I_D = 7.5 A
Rise time	tr	—	30	—	ns	V_{GS} = 10 V
Turn-off delay time	td(off)	—	120	—	ns	R_L = 33.3 Ω
Fall time	tf	—	50	—	ns	Rg = 10 Ω
Total gate charge	Qg	—	48	—	nC	V_{DD} = 400 V
Gate to source charge	Qgs	—	10	—	nC	V_{GS} = 10 V
Gate to drain charge	Qgd	—	24	—	nC	I_D = 15 A
Body-drain diode forward voltage	V_{DF}	—	0.85	1.3	V	I_F = 15 A, V_{GS} = 0
Body-drain diode reverse recovery time	trr	—	500	—	ns	I_F = 15 A, V_{GS} = 0
Body-drain diode reverse recovery charge	Qrr	—	20	—	μC	diF/dt = 100 A/μs

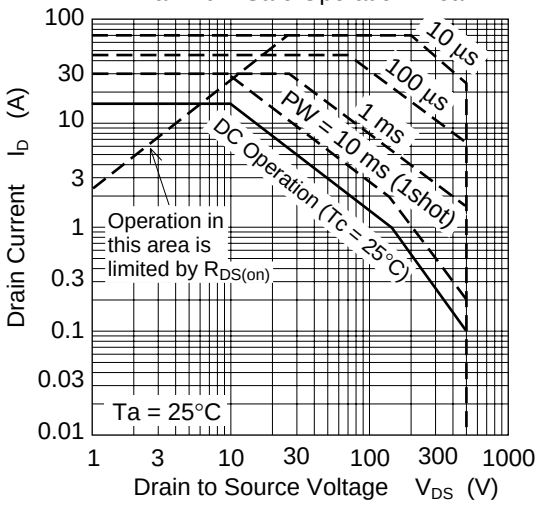
Note: 4. Pulse test

Main Characteristics

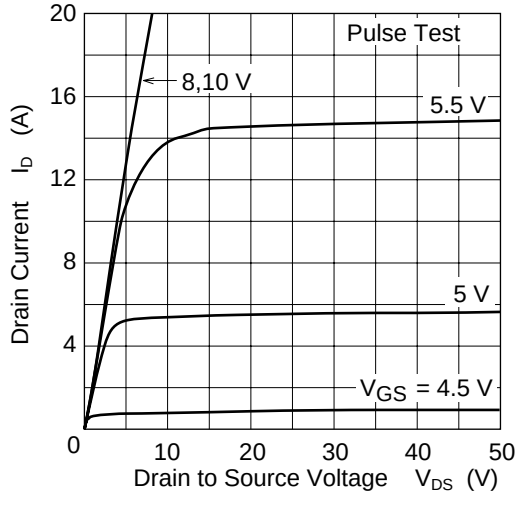
Power vs. Temperature Derating



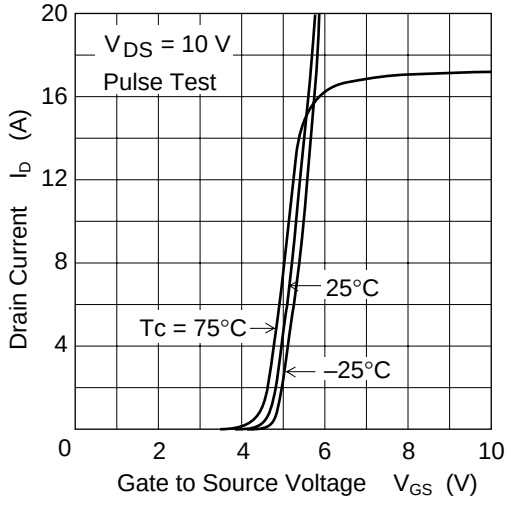
Maximum Safe Operation Area



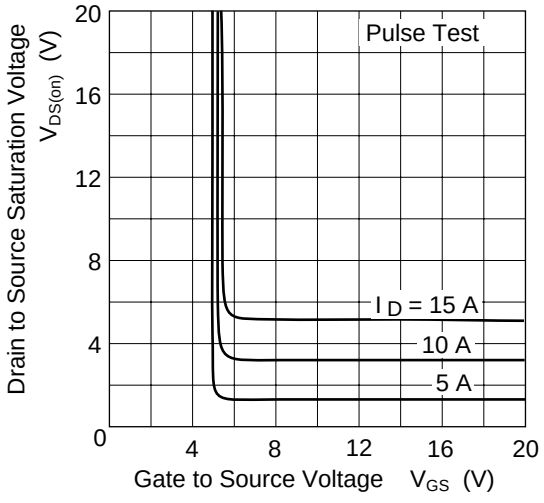
Typical Output Characteristics



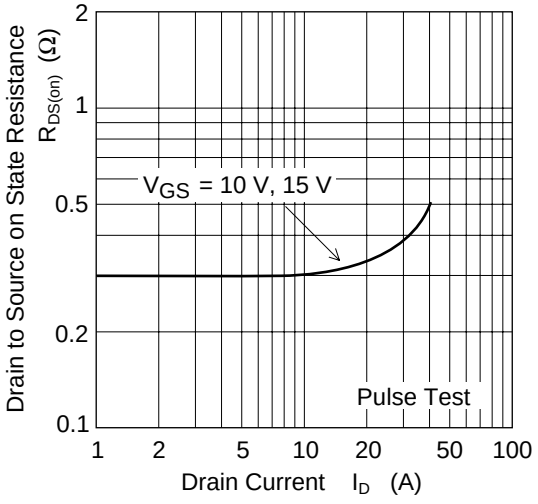
Typical Transfer Characteristics



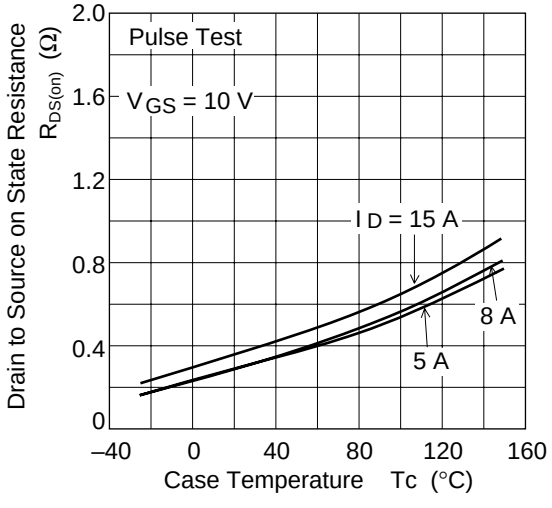
Drain to Source Saturation Voltage vs. Gate to Source Voltage



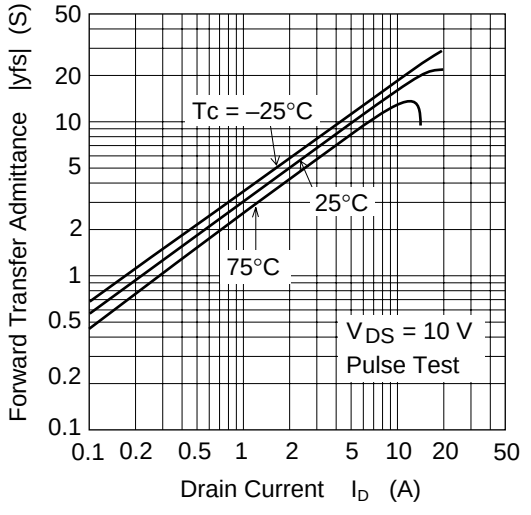
Static Drain to Source on State Resistance vs. Drain Current



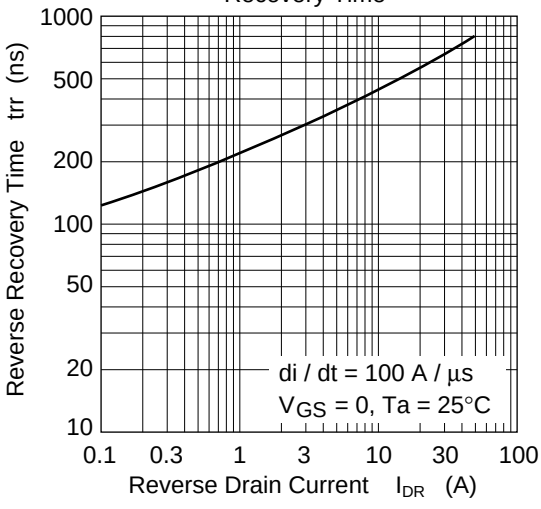
Static Drain to Source on State Resistance vs. Temperature



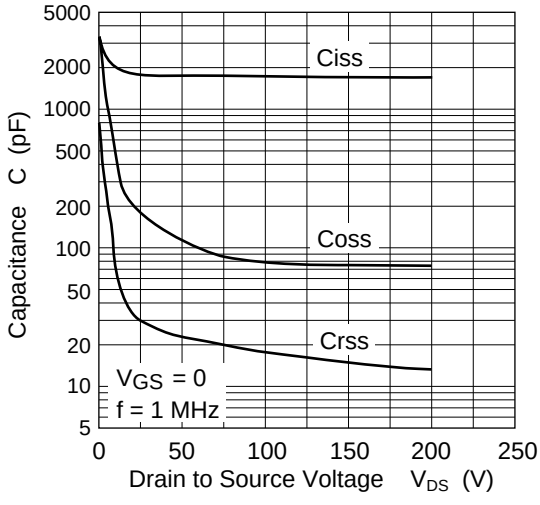
Forward Transfer Admittance vs. Drain Current



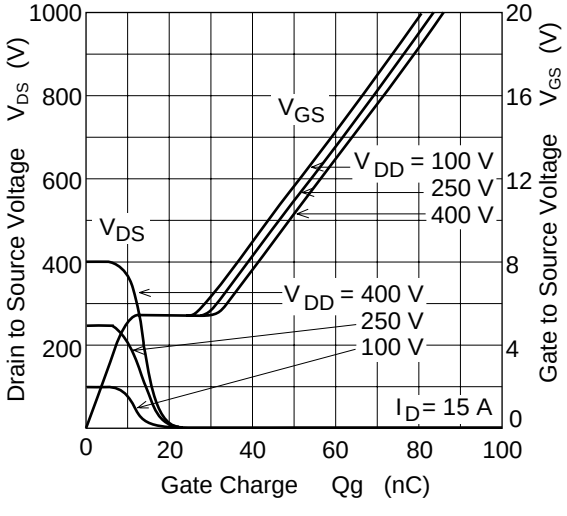
Body-Drain Diode Reverse Recovery Time



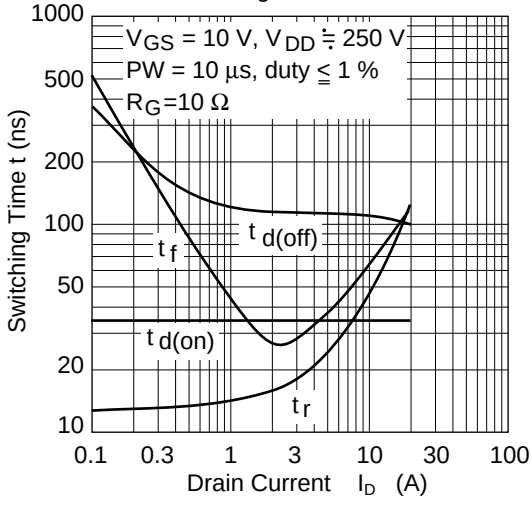
Typical Capacitance vs. Drain to Source Voltage



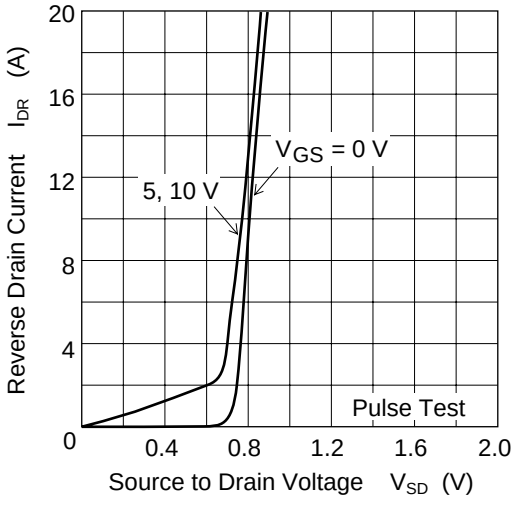
Dynamic Input Characteristics



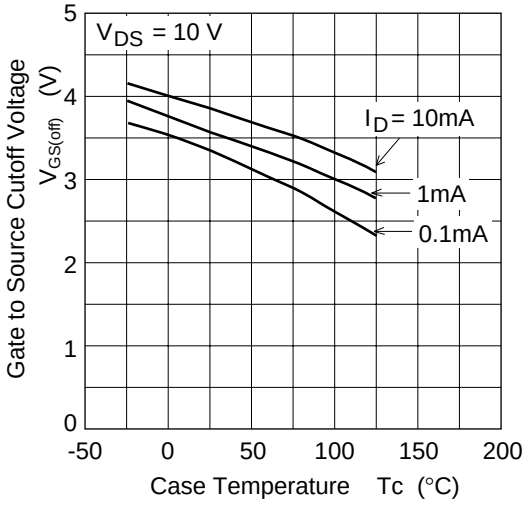
Switching Characteristics



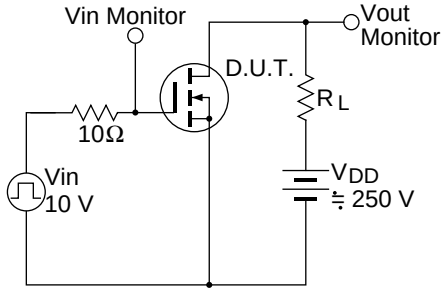
Reverse Drain Current vs.
Source to Drain Voltage



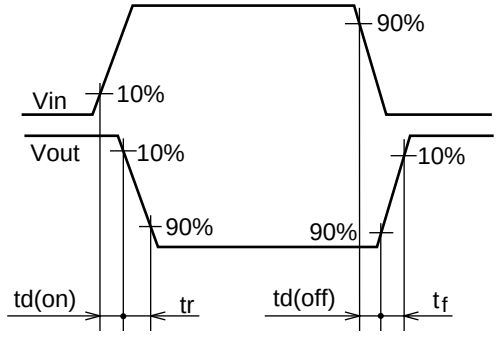
Gate to Source Cutoff Voltage
vs. Case Temperature

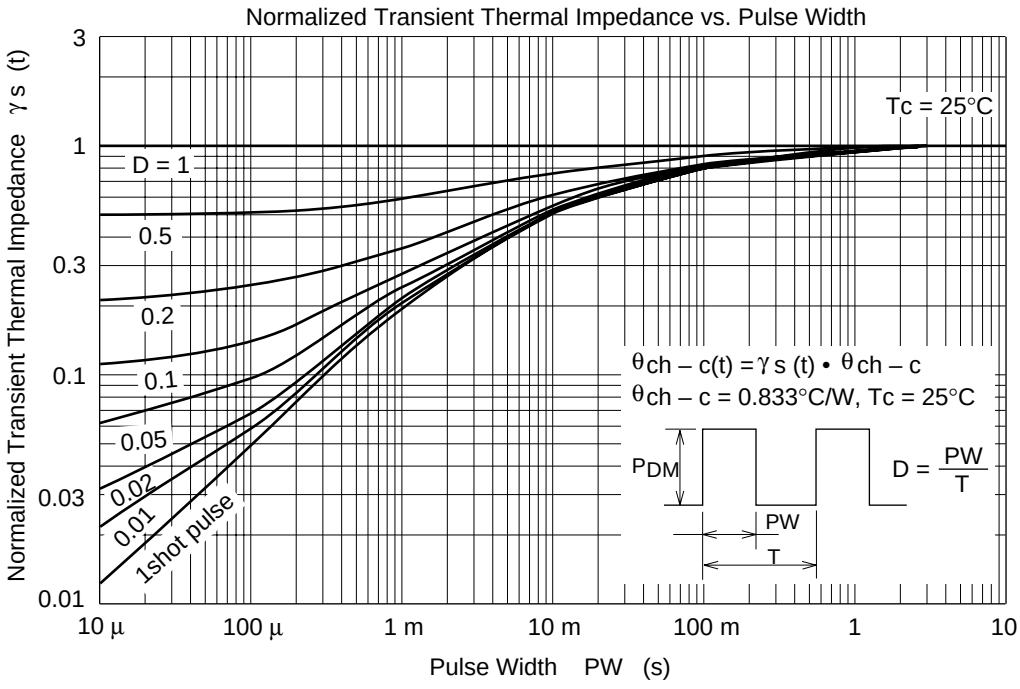


Switching Time Test Circuit



Waveform

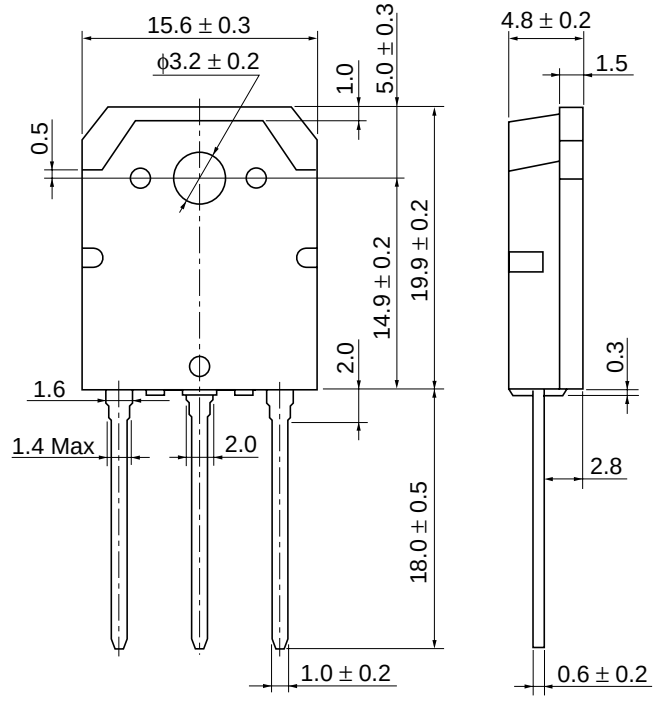


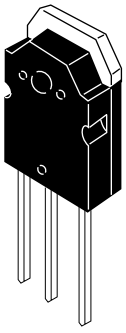

Normalized Transient Thermal Impedance vs. Pulse Width
Normalized Transient Thermal Impedance γs (t)
Pulse Width PW (s)
Tc = 25°C
D = 1
0.5
0.2
0.1
0.05
0.02
0.01
1shot pulse
θch – c(t) = γs (t) • θch – c
θch – c = 0.833°C/W, Tc = 25°C
PDM
D = PW/T
PW
T
3
1
0.3
0.1
0.03
0.01
10 µ
100 µ
1 m
10 m
100 m
1
10

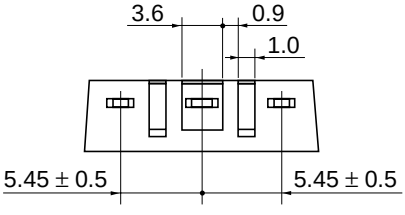
Package Dimensions

As of January, 2001

Unit: mm







Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Mass (reference value)	5.0 g

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